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Zn1-xAlxO:NiO Composite Transparent Conducting Oxide Thin Film/p-Type Silicon Photodiodes

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JOURNAL OF NANOELECTRONICS AND OPTOELECTRONICS

Volume: 10 Issue: 6 Pages: 739-744

DOI: 10.1166/jno.2015.1664

Published: DEC 2015

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Abstract

Zn1-xAlxO:NiO composite transparent conducting oxide thin films were prepared by sol gel method to prepare Zn1-xAlxO:NiO/p-type silicon photodiodes. The structural properties of the films were analyzed by AFM measurements. The diodes were coated on p-type silicon having ohmic contact by sol gel spin coating method. The ideality factor and barrier height values of the diodes were obtained. The photoresponse properties of the diodes were performed under solar light illuminations. It was found that the photocurrent of the diodes is higher than the dark current. This indicates that the diodes exhibited a photodiode behavior. The obtained results indicate that the photoresponse properties of Zn1-xAlxO:NiO composite transparent conducting oxide thin film/p-type silicon photodiodes are controlled by NiO doping.

Keywords

Author Keywords: Transparent Conducting Oxide Thin Film; Photodiode

KeyWords Plus: BARRIER DIODES SBDS; SERIES RESISTANCE; SCHOTTKY DIODES; PHOTOCONDUCTING PROPERTIES; ELECTRICAL-PROPERTIES; INTERFACE STATES; CAPACITANCE; FREQUENCY; SEMICONDUCTOR; ELECTRODES

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Funding

| Funding Agency | Grant Number |
|--------------------------------------------------------------------------|---------------|
| Deanship of Scientific Research (DSR), King Abdulaziz University, Jeddah | 615-130-D1435 |

[View funding text](#)

Publisher

AMER SCIENTIFIC PUBLISHERS, 26650 THE OLD RD, STE 208, VALENCIA, CA 91381-0751 USA

Categories / Classification

Research Areas: Engineering; Science & Technology - Other Topics; Physics

Web of Science Categories: Engineering, Electrical & Electronic; Nanoscience & Nanotechnology; Physics, Applied

Document Information

Document Type: Article

Language: English

Accession Number: WOS:000362695400005

ISSN: 1555-130X

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